

Features

- $BV_{CEO} > -40V$
- $I_C = -200mA$ Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary NPN Type: MMST3904
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

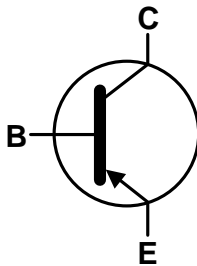
Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 $\text{\textcircled{E}}$
- Weight: 0.006 grams (Approximate)

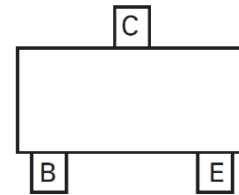
SOT323



Top View



Device Symbol



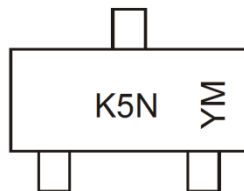
Pin-out Top View

Ordering Information (Note 4)

Product	Status	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMST3906-7-F	Active	AEC-Q101	K5N	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



K5N = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: D = 2016)
 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	
Code	C	D	E	F	G	H	I	J	K	L	M	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Absolute Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-200	mA

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _d	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes: 5. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

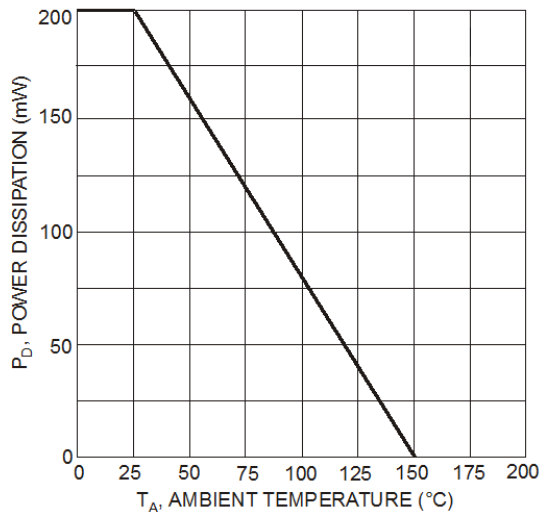


Fig. 1 Max Power Dissipation vs. Ambient Temperature

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	BV_{CBO}	-40	—	V	$I_C = -10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-40	—	V	$I_C = -1\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	—	V	$I_E = -10\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CEX}	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3\text{V}$
Base Cutoff Current	I_{BL}	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3\text{V}$
ON CHARACTERISTICS (Note 7)					
DC Current Gain	h_{FE}	60	—	—	$I_C = -100\mu\text{A}, V_{CE} = -1\text{V}$ $I_C = -1\text{mA}, V_{CE} = -1\text{V}$ $I_C = -10\text{mA}, V_{CE} = -1\text{V}$ $I_C = -50\text{mA}, V_{CE} = -1\text{V}$ $I_C = -100\text{mA}, V_{CE} = -1\text{V}$
		80	—		
		100	300		
		60	—		
		30	—		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	-0.20 -0.30	V	$I_C = -10\text{mA}, I_B = -1\text{mA}$ $I_C = -50\text{mA}, I_B = -5\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-0.65 —	-0.85 -0.95	V	$I_C = -10\text{mA}, I_B = -1\text{mA}$ $I_C = -50\text{mA}, I_B = -5\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{OBO}	—	4.5	pF	$V_{CB} = -5\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{IBO}	—	10	pF	$V_{EB} = -0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Input Impedance	h_{iE}	2	12	k Ω	$V_{CE} = 1\text{V}, I_C = 10\text{mA},$ $f = 1\text{kHz}$
Voltage Feedback Ratio	h_{rE}	0.1	10	$\times 10^{-4}$	
Small Signal Current Gain	H_{FE}	100	400	—	
Output Admittance	h_{oE}	3	60	μS	
Current Gain-Bandwidth Product	f_T	300	—	MHz	
Noise Figure	NF	—	4	dB	$V_{CE} = -20\text{V}, I_C = -10\text{mA},$ $f = 100\text{MHz}$ $V_{CE} = -5\text{V}, I_C = -100\mu\text{A},$ $R_S = 1\text{k}\Omega, f = 1\text{kHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	35	ns	$V_{CC} = -3\text{V}, I_C = -10\text{mA},$ $I_{B1} = -1\text{mA}, V_{BE(off)} = 0.5\text{V}$
Rise Time	t_r	—	35	ns	
Storage Time	t_s	—	225	ns	$V_{CC} = -3\text{V}, I_C = -10\text{mA},$ $I_{B1} = I_{B2} = -1\text{mA}$
Fall Time	t_f	—	75	ns	

Note: 7. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

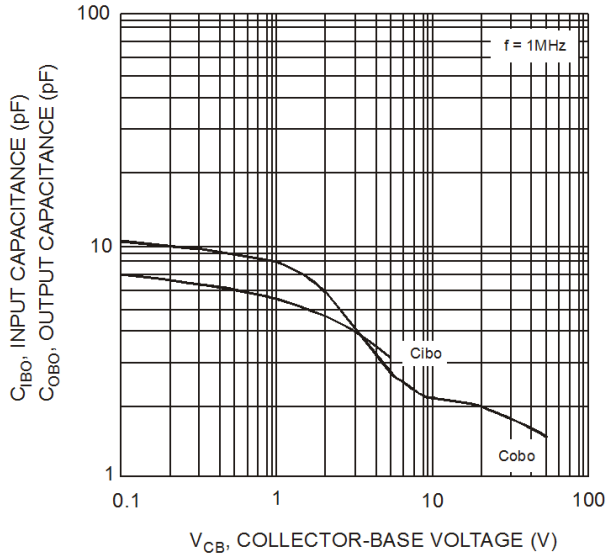


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

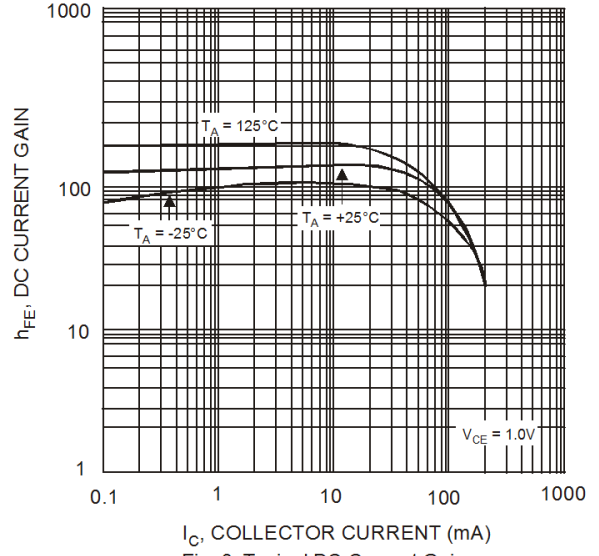


Fig. 3, Typical DC Current Gain vs. Collector Current

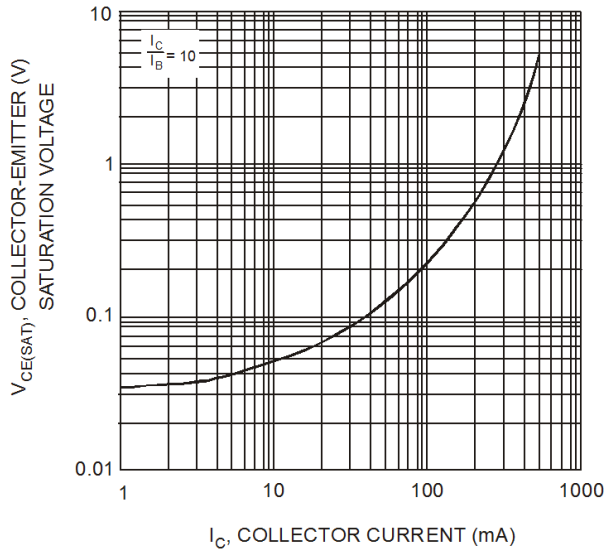


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

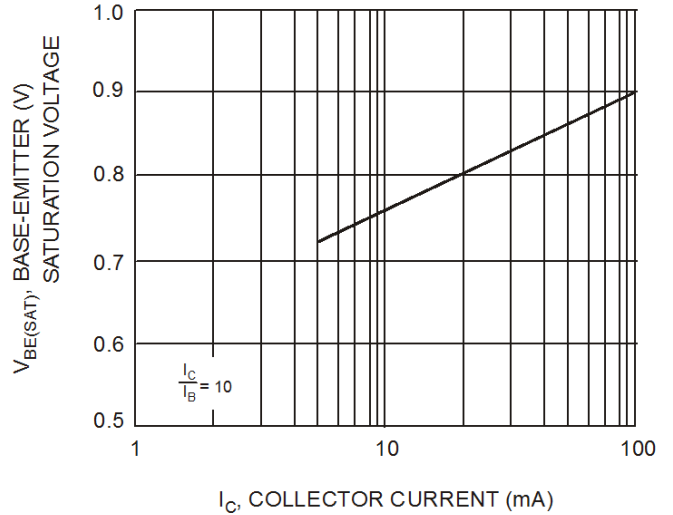
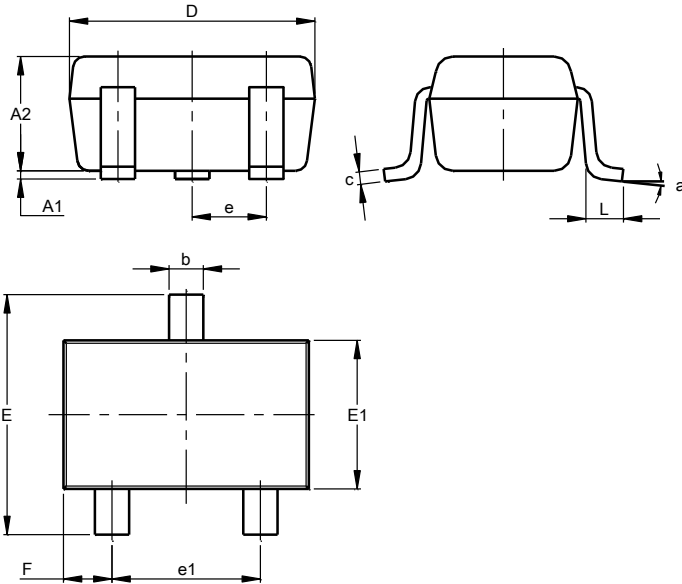


Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

Package Outline Dimensions

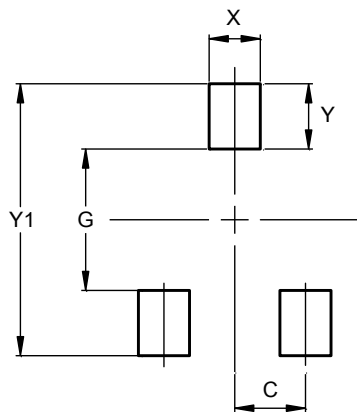
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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